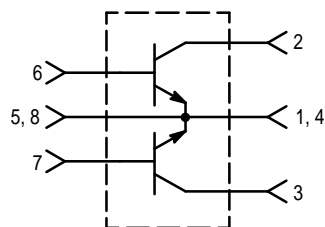


The RF Line

NPN Silicon Push-Pull RF Power Transistor

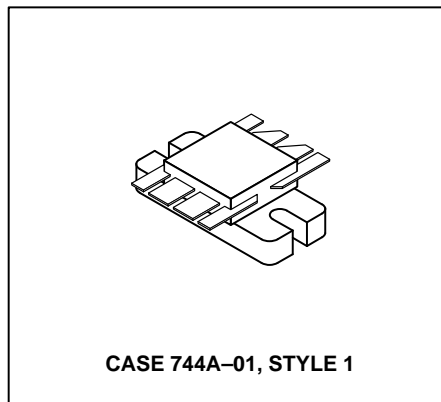
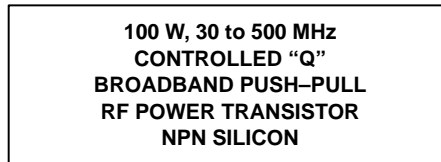
... designed primarily for wideband large-signal output and driver amplifier stages in the 30 to 500 MHz frequency range.

- Specified 28 Volt, 500 MHz Characteristics —
Output Power = 100 W
Typical Gain = 9.5 dB (Class AB); 8.5 dB (Class C)
Efficiency = 55% (Typ)
- Built-In Input Impedance Matching Networks for Broadband Operation
- Push-Pull Configuration Reduces Even Numbered Harmonics
- Gold Metallization System for High Reliability
- 100% Tested for Load Mismatch



The MRF393 is two transistors in a single package with separate base and collector leads and emitters common. This arrangement provides the designer with a space saving device capable of operation in a push-pull configuration.

PUSH-PULL TRANSISTORS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	16	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	270 1.54	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	$^\circ\text{C/W}$

NOTE:

1. This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF push-pull amplifier.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (1)					
Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 50\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 5.0\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	5.0	mAdc

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	—	100	—
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DYNAMIC CHARACTERISTICS (1)

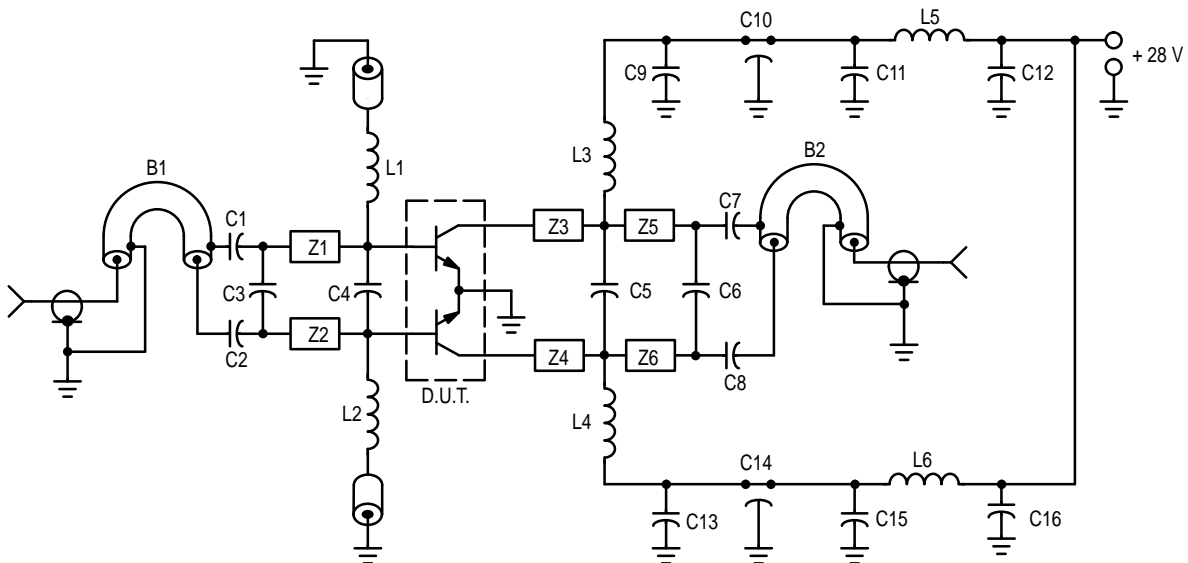
Output Capacitance ($V_{CB} = 28\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	40	75	95	pF
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FUNCTIONAL TESTS (2) — See Figure 1

Common–Emitter Amplifier Power Gain ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$)	G_{pe}	7.5	8.5	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$)	η	50	55	—	%
Load Mismatch ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 100\text{ W}$, $f = 500\text{ MHz}$, $VSWR = 30:1$, all phase angles)	ψ	No Degradation in Output Power			

NOTES:

- Each transistor chip measured separately.
- Both transistor chips operating in push–pull amplifier.



C1, C2, C7, C8 — 240 pF 100 mil Chip Cap
 C3 — 15 pF 100 mil Chip Cap
 C4 — 24 pF 100 mil Chip Cap
 C5 — 33 pF 100 mil Chip Cap
 C6 — 12 pF 100 mil Chip Cap
 C9, C13 — 1000 pF 100 mil Chip Cap
 C10, C14 — 680 pF Feedthru Cap
 C11, C15 — 0.1 μF Ceramic Disc Cap
 C12, C16 — 50 μF 50 V

L1, L2 — 0.15 μH Molded Choke with Ferrite Bead
 L3, L4 — 2–1/2 Turns #20 AWG 0.200" ID
 L5, L6 — 3–1/2 Turns #18 AWG 0.200" ID

B1, B2 — Balun 50 Ω Semi Rigid Coax, 86 mil OD, 4" Long

Z1, Z2 — 850 mil Long x 125 mil W. Microstrip
 Z3, Z4 — 200 mil Long x 125 mil W. Microstrip
 Z5, Z6 — 800 mil Long x 125 mil W. Microstrip

Board Material — 0.0325" Teflon–Fiberglass, $\epsilon_r = 2.56$,
 1 oz. Copper Clad both sides.

Figure 1. 500 MHz Test Fixture

CLASS C

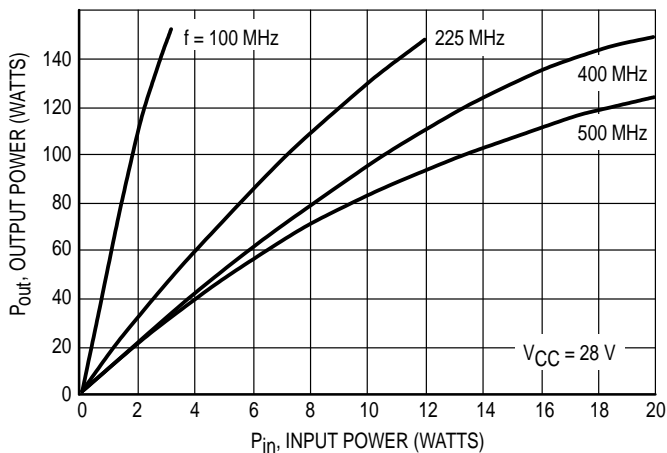


Figure 2. Output Power versus Input Power

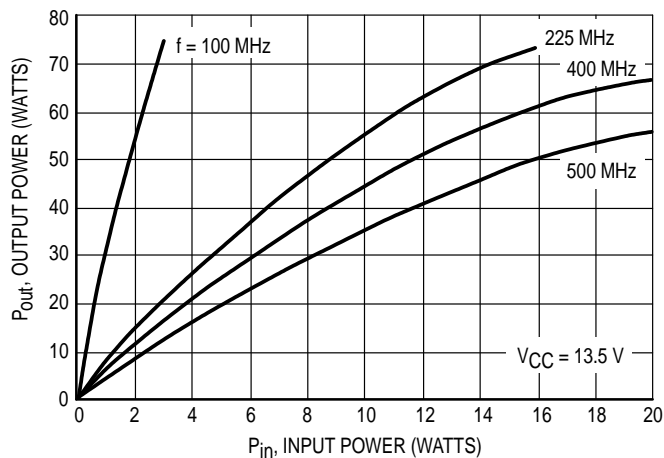


Figure 3. Output Power versus Input Power

CLASS C

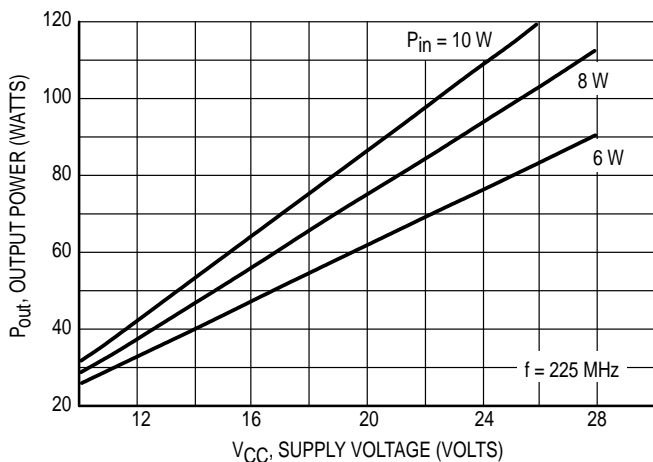


Figure 4. Output Power versus Supply Voltage

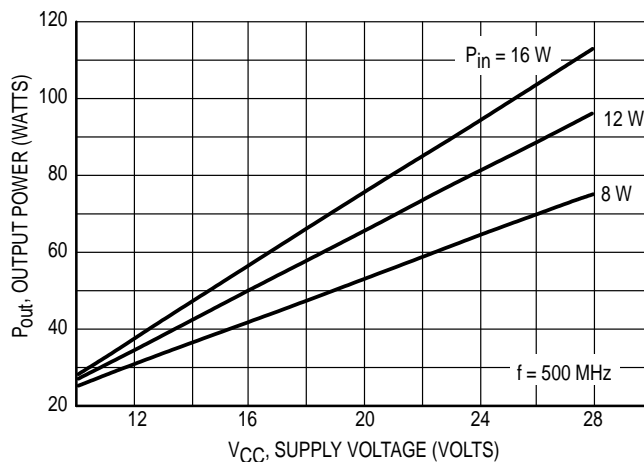
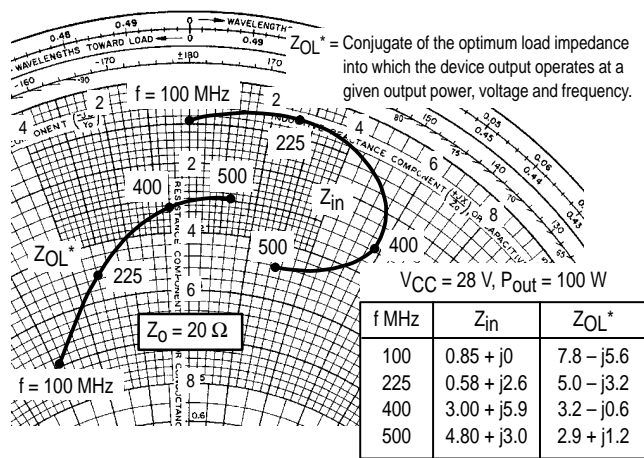


Figure 5. Output Power versus Supply Voltage



NOTE: Z_{in} & Z_{OL}* are given from base-to-base and collector-to-collector respectively.

Figure 6. Series Equivalent Input/Output Impedance

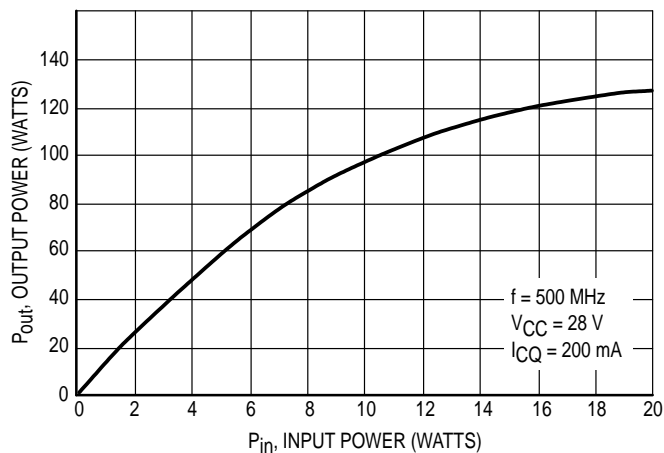
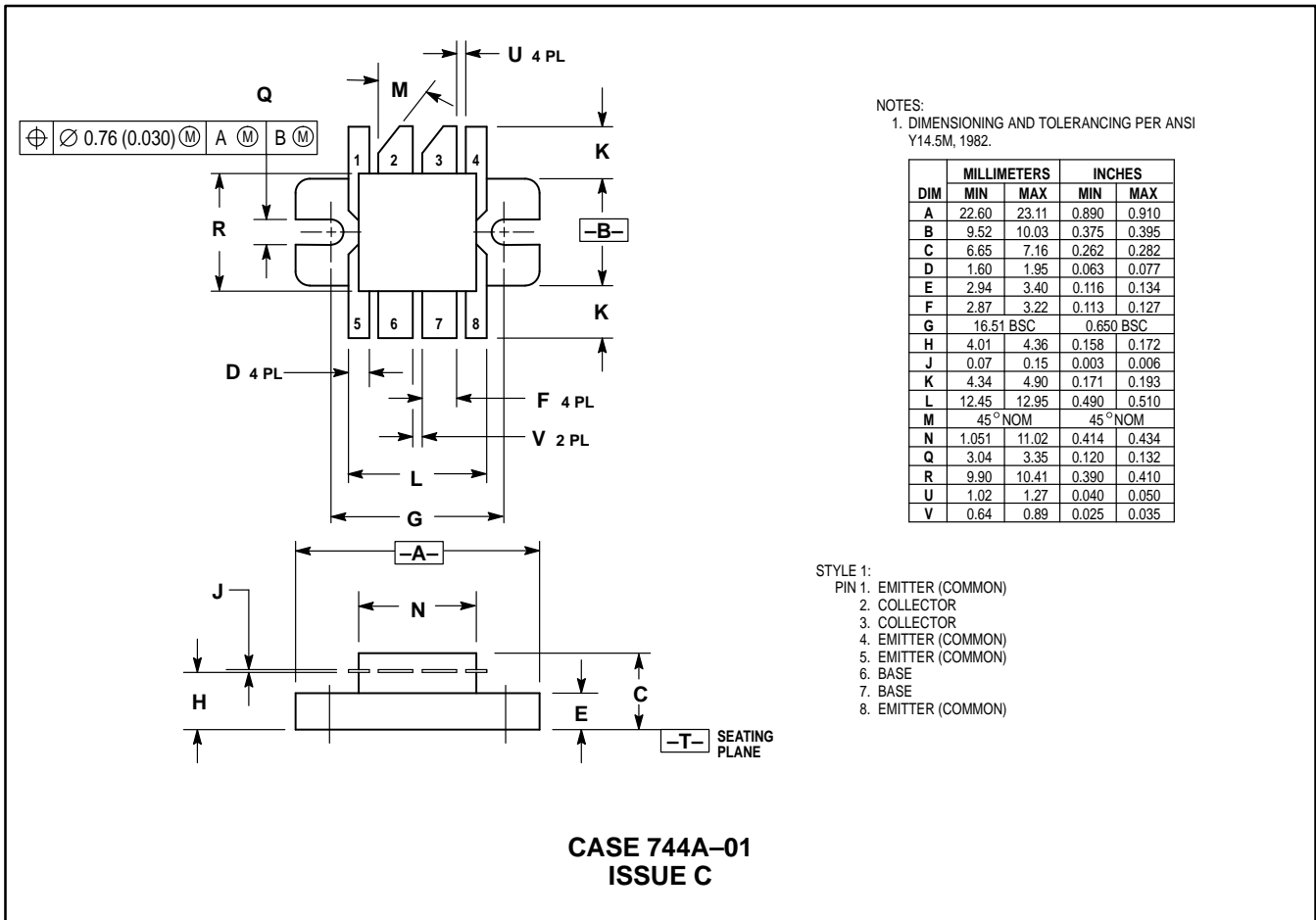


Figure 7. Class AB Output Power versus Input Power

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	22.60	23.11	0.890	0.910
B	9.52	10.03	0.375	0.395
C	6.65	7.16	0.262	0.282
D	1.60	1.95	0.063	0.077
E	2.94	3.40	0.116	0.134
F	2.87	3.22	0.113	0.127
G	16.51 BSC		0.650 BSC	
H	4.01	4.36	0.158	0.172
J	0.07	0.15	0.003	0.006
K	4.34	4.90	0.171	0.193
L	12.45	12.95	0.490	0.510
M	45° NOM		45° NOM	
N	1.051	11.02	0.414	0.434
Q	3.04	3.35	0.120	0.132
R	9.90	10.41	0.390	0.410
U	1.02	1.27	0.040	0.050
V	0.64	0.89	0.025	0.035

- STYLE 1:
 PIN 1: EMITTER (COMMON)
 2: COLLECTOR
 3: COLLECTOR
 4: EMITTER (COMMON)
 5: EMITTER (COMMON)
 6: BASE
 7: BASE
 8: EMITTER (COMMON)

Specifications subject to change without notice.

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